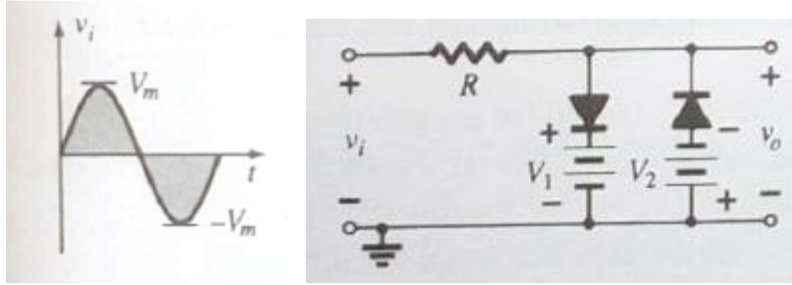


1a. Analyse the circuit and draw the pattern of the output ( $V_o$ ) of the circuit shown in figure, Provided  $V_m=10V$  and  $V_1, V_2=5V$ .



During +ve half cycle

\* Diode  $D_2$  is always reverse bias & acts as open ckt.

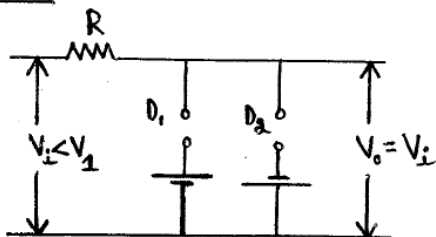
Case i: When  $V_i < V_1$ , diode  $D_1$  is reverse bias & acts as open ckt.

Thus o/p  $V_o = V_i$

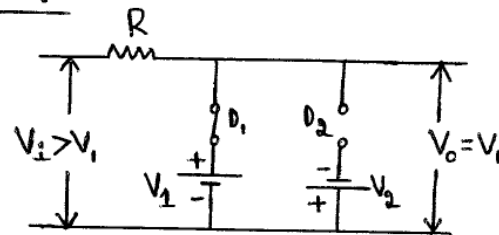
Case ii: When  $V_i > V_1$ , diode  $D_1$  is forward bias & acts as short ckt.

Thus o/p  $V_o = V_1$

Case i:



Case ii:



During -ve half cycle

\* Diode  $D_1$  is always reverse bias & acts as open ckt.

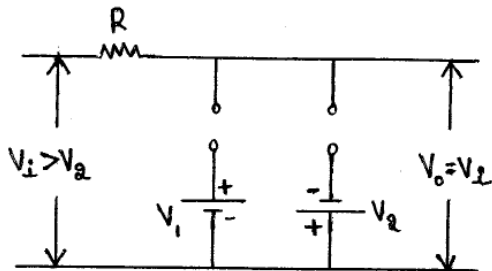
Case i: When  $V_i > V_2$ , diode  $D_2$  is reverse bias & acts as open ckt.

Thus o/p  $V_o = V_i$

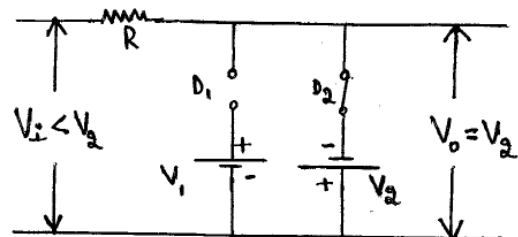
Case ii : When  $V_i < V_2$ , diode  $D_2$  is forward bias & acts as short ckt.

Thus o/p  $V_o = V_2$

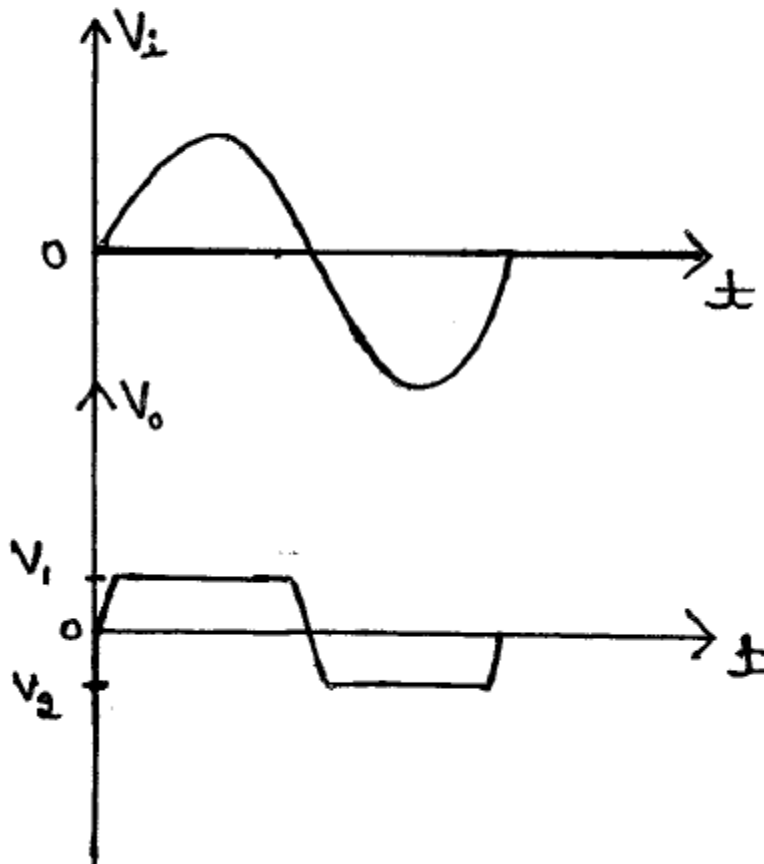
Case i :



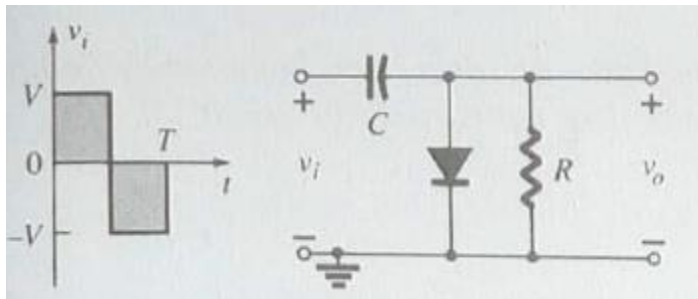
Case ii :



I/o Waveforms:



1b. Analyse the circuit and draw the pattern of the output ( $V_o$ ) of the circuit shown in figure .



2. What are the different biasing circuits? Find the expression for stability factor  $S(I_{CBO})$  of each biasing circuit?

1) Fixed - Bias circuit :-

> For fixed-bias ckt, the base current is given by

$$I_B = \frac{V_{CC} - V_{BE}}{R_B} \rightarrow \textcircled{1}$$

Differentiating eq 1 w.r.t. to  $I_C$ , we get

$$\frac{dI_B}{dI_C} = 0 \rightarrow \textcircled{2}$$

Sub eq ② in stability factor equation

$$S = \frac{(1+\beta)}{1 - \beta \left( \frac{dI_B}{dI_C} \right)} = \frac{(1+\beta)}{1 - \beta(0)} = \frac{1+\beta}{1}$$

$$\boxed{S = 1 + \beta}$$

Emitter stabilized bias :-

$$i) S = S_{(I_{CBO})} = \frac{dI_B}{dI_C}$$

From emitter stabilized bias ckt we have.

$$V_{CC} = I_B R_B + V_{BE} + I_E R_E \rightarrow (1)$$

$$W \cdot K \cdot T$$

$$V_{CC} = I_B R_B + V_{BE} + (I_C + I_B) R_E$$

$$I_E = I_C + I_B$$

$$V_{CC} = \underline{I_B R_B} + V_{BE} + I_C R_E + \underline{I_B R_E}$$

$$V_{CC} = I_B (R_B + R_E) + I_C R_E + V_{BE} \rightarrow (2)$$

$$(I_B (R_B + R_E) = V_{CC} - I_C R_E - V_{BE})$$

diff Eq (2) w.r. to  $I_C$

$$0 = \frac{dI_B}{dI_C} (R_B + R_E) + \frac{dI_C}{dI_C} (R_E) + 0$$

$$\frac{dI_B}{dI_C} (R_B + R_E) = -R_E$$

$$\therefore \frac{dI_B}{dI_C} = \frac{-R_E}{R_B + R_E}$$

$$\therefore S_{I_{CBO}} = \frac{1 + \beta}{1 - \beta \left( \frac{-R_E}{R_B + R_E} \right)}$$

$$S_{I_{CBO}} = \frac{1 + \beta}{1 + \beta \left[ \frac{R_E}{R_B + R_E} \right]}$$

Voltage divider bias :-

$$S(I_{CBO}) = \frac{dI_B}{dI_C}$$

From voltage divider bias circuit, we have,

$$V_{Th} = I_B R_{Th} + V_{BE} + I_E R_E \rightarrow \textcircled{1}$$

$W.K.T$

$$I_E = I_B + I_C$$

$$V_{Th} = I_B R_{Th} + V_{BE} + I_B R_E + I_C R_E$$

$$V_{Th} = V_{BE} + I_B (R_{Th} + R_E) + I_C R_E \rightarrow \textcircled{2}$$

diff eq  $\textcircled{2}$  w.r.to  $I_C$ .

$$0 = 0 + \frac{dI_B}{dI_C} (R_{Th} + R_E) + \frac{dI_C}{dI_C} R_E$$

$$\frac{dI_B}{dI_C} (R_{Th} + R_E) = -R_E$$

$$\frac{dI_B}{dI_C} = -\frac{R_E}{R_{Th} + R_E}$$

$$\therefore S(I_{CBO}) = \frac{1 + \beta}{1 - \beta \left( \frac{dI_B}{dI_C} \right)}$$

$$S(I_{CBO}) = \frac{1 + \beta}{1 + \beta \left[ \frac{R_E}{R_{Th} + R_E} \right]}$$

where,

$$R_{Th} = R_1 \parallel R_2$$

3. Draw the circuit of voltage divider bias circuit. The circuit parameters are,

$V_{cc} = 10V$ ,  $R_2 = 17 k\Omega$ ,  $R_1 = 83 k\Omega$ ,  $R_c = 2 k\Omega$ ,  $R_E = 0.5 k\Omega$ , find Q-point and terminal voltages. The transistor has  $\beta = 100$  and  $V_{BE} = 0.7V$

4a. Explain the reasons for instability of Operating point.

**Reasons for Instability of the operating point :-**

**1. Variation of leakage current ' $I_{CO}$ ' with temperature:-**

The reverse saturation current ' $I_{CO}$ ' doubles for every 10°C increase in temperature.

**2. Variation of base-emitter voltage ' $V_{BE}$ ' with temperature :-**

$V_{BE}$  decreases by 2.5mv for every 1°C rise in temperature.

**3. Variation of current gain ' $\beta$ ' with temperature :-**

$\beta$  increases with rise in the temperature.

4b. Describe procedure to find the Q-point of a BJT circuit.

5a. Mention the applications of clippers and clampers.

**Clippers find several applications, such as**

- They are frequently used for the separation of synchronizing signals from the composite picture signals.
- The excessive noise spikes above a certain level can be limited or clipped in FM transmitters by using the series clippers.
- For the generation of new waveforms or shaping the existing waveform, clippers are used.
- The typical application of diode clipper is for the protection of transistor from transients, as a freewheeling diode connected in parallel across the inductive load.
- Frequently used **half wave rectifier** in power supply kits is a typical example of a clipper. It clips either positive or negative half wave of the input.
- Clippers can be used as voltage limiters and amplitude selectors.

**Clampers can be used in applications**

- The complex transmitter and receiver circuitry of television clamper is used as a **base line stabilizer** to define sections of the luminance signals to preset levels.
- Clampers are also called as direct current restorers as they clamp the wave forms to a fixed DC potential.
- These are frequently used in test equipment, sonar and **radar systems**.
- For the protection of the **amplifiers** from large errant signals clampers are used.
- Clampers can be used for removing the distortions
- For improving the overdrive recovery time clampers are used.
- Clampers can be used as voltage doublers or **voltage multipliers**.

5b. Design emitter bias circuit using the following specifications:

$I_{C(sat)} = 10\text{mA}$ ,  $I_{CQ} = 0.5 I_{C(sat)}$ ,  $V_C = 20\text{V}$ ,  $V_{CC} = 30\text{V}$ . Assume silicon transistor with  $\beta = 100$

**Calculation of  $R_C$**

$$I_{CQ} = I_C = \frac{1}{2} I_{C(\text{sat})} = 5 \text{ mA}$$

$$R_C = \frac{V_{CC} - V_C}{I_C} = \frac{30 \text{ V} - 20 \text{ V}}{5 \text{ mA}} = 2 \text{ k}\Omega$$

**Calculation of  $R_E$**

$$I_{C(\text{sat})} = \frac{V_{CC}}{R_C + R_E}$$

$$R_C + R_E = \frac{V_{CC}}{I_{C(\text{sat})}} = \frac{30 \text{ V}}{10 \text{ mA}} = 3 \text{ k}\Omega$$

$$R_E = 3 \text{ k}\Omega - R_C = 1 \text{ k}\Omega$$

**Calculation of  $R_B$**

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (1 + \beta)R_E}$$

$$I_B = \frac{I_C}{\beta} = \frac{5 \text{ mA}}{100} = 50 \mu\text{A}$$

Using this value in Equation (A) we have,

$$50 \mu\text{A} = \frac{30 \text{ V} - 0.7 \text{ V}}{R_B + (101)(1 \text{ k}\Omega)}$$

$$R_B + 101 \text{ k}\Omega = 586 \text{ k}\Omega$$

$$R_B = 586 \text{ k}\Omega - 101 \text{ k}\Omega = 485 \text{ k}\Omega$$

6. Design a voltage divider bias circuit with  $V_{CC} = 10\text{V}$ ,  $R_C = 1.5 \text{ k}\Omega$ ,

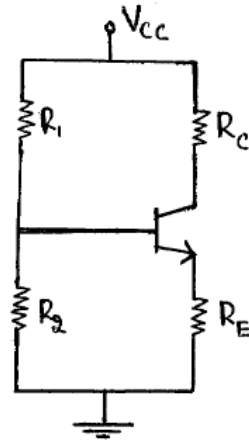
$I_C = 2\text{mA}$ ,  $V_{CE} = 5\text{V}$ ,  $\beta = 50$ . Assume silicon transistor and stability factor = 5

Given:

$$V_{CC} = 10V, R_C = 1.5k\Omega, I_C = 2mA, V_{CE} = 5V, V_{BE} = 0.7V$$

$$\beta = 50 \text{ \& } S = 5.$$

$$R_1 = ?, R_2 = ? \text{ \& } R_E = ?.$$



Sol:-

$$* I_B = \frac{I_C}{\beta} = \frac{2mA}{50} = 40\mu A$$

$$* I_E = I_B + I_C = 40\mu A + 2mA = 2.04mA$$

$$* R_E = \frac{V_{CC} - V_{CE} - I_C R_C}{I_E} = \frac{10V - 5V - [2mA \times 1.5k\Omega]}{2.04mA} = 980.39\Omega$$

$$* V_E = I_E R_E = 2.04mA \times 980.39\Omega = 1.999V$$

$$* S = 1 + \frac{R_{TH}}{R_E}$$

$$5 = 1 + \frac{R_{TH}}{R_E}$$

$$4 = \frac{R_{TH}}{R_E}$$

$$R_{TH} = 4R_E = 4 \times 980.39\Omega$$

$$R_{TH} = 3.92k\Omega$$

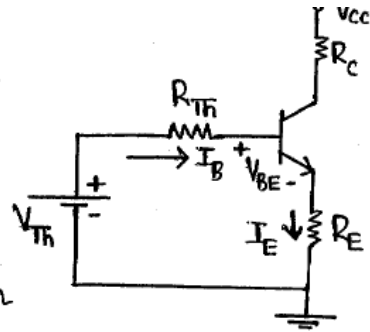


\* Applying KVL to the CKT, we get

$$V_{TH} - I_B R_{TH} - V_{BE} - I_E R_E = 0$$

$$V_{TH} = I_B R_{TH} + V_{BE} + I_E R_E$$

$$= 40 \mu A \times 3.92k\Omega + 0.7V + 2.04mA \times 980.34\Omega$$



$$V_{TH} = 2.856V$$

\* WKT

$$V_{TH} = \frac{R_2}{R_1 + R_2} V_{CC}$$

$$\frac{R_2}{R_1 + R_2} = \frac{V_{TH}}{V_{CC}}$$

$$\frac{R_2}{R_1 + R_2} = \frac{2.856V}{10V}$$

$$\frac{R_2}{R_1 + R_2} = 0.2856V \rightarrow \textcircled{1}$$

\* WKT  $R_{TH} = \frac{R_1 R_2}{R_1 + R_2} \rightarrow \textcircled{2}$

Substituting eq ① in eq ②, we get

$$R_{TH} = R_1 \times 0.2856$$

$$R_1 = \frac{R_{TH}}{0.2856} = \frac{3.92k\Omega}{0.2856}$$

$$R_1 = 13.72k\Omega$$

Substituting 'R<sub>1</sub>' value in eq ①, we get

ie.  $\frac{R_2}{R_1 + R_2} = 0.2856V \leftarrow \textcircled{1}$

$$\frac{R_1 + R_2}{R_2} = \frac{1}{0.28568}$$

$$\frac{R_1}{R_2} + \frac{\cancel{R_2}}{\cancel{R_2}} = 3.50042$$

$$\frac{R_1}{R_2} + 1 = 3.50042$$

$$\frac{R_1}{R_2} = 3.50042 - 1$$

$$\frac{R_1}{R_2} = 2.50042$$

$$R_2 = \frac{R_1}{2.50042} = \frac{13.72 \text{ k}\Omega}{2.50042}$$

$$R_2 = 5.48 \text{ k}\Omega$$

